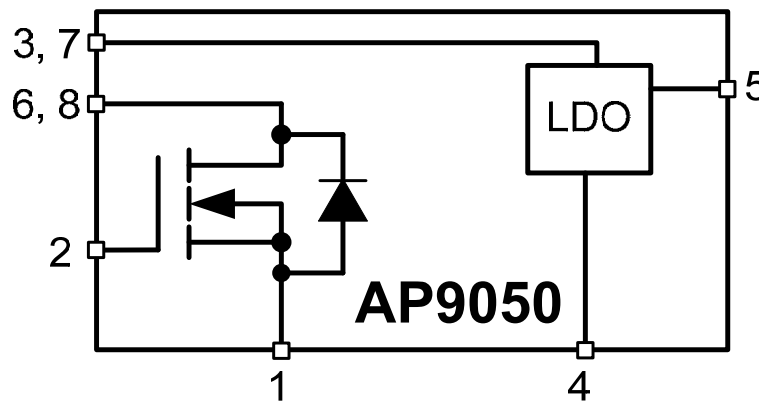




**Pin Descriptions**

Pin #	Name	Description
1	Source	Source of the n-channel power FET. Pass-switch's output pin.
2	Gate	Gate of the FET switch. Pass-switch's control pin.
3, 7	V <sub>IN</sub>	Input voltage to the internal LDO.
4	Ground	LDO ground connection.
5	V <sub>OUT</sub>	Output of the LDO.
6, 8	Drain	Drain of the power FET. Pass-switch's input pin.

**Functional Block Diagram**



**Figure 2. Functional Block Diagram**

### Absolute Maximum Ratings (Note 2, 3)

Symbol	Parameter	Rating	Unit
$V_{IN}$	Supply Voltage	-0.3 to 30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_{Dpk}$	Drain Current, Peak (10 $\mu$ s pulse)	19	A
$I_D$	Drain Current, Continuous (Note 4, Steady-State) $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	3.7 2.7	A
$P_{max}$	Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 3, 4)	750	mW
$T_J$	Junction Temperature Range	-40 to +125	$^\circ\text{C}$
$T_J$	Non-operating Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purposes	260	$^\circ\text{C}$

Semiconductor devices are ESD sensitive and may be damaged by exposure to ESD events. Suitable ESD precautions should be taken when handling and transporting these devices.

- Notes:
2. Exceeding these ratings may damage the device.
  3. Mounted on FR4 Board using 30 mm<sup>2</sup>, 2 oz Cu.
  4. Dual die operation (equally-heated).

### Thermal Resistance

Symbol	Parameter	Rating	Unit
$\theta_{JA}$	Junction to Ambient (Note 5)	132	$^\circ\text{C}/\text{W}$
$\theta_{JC}$	Junction to Case	13	$^\circ\text{C}/\text{W}$

Note: 5. Test condition for DFN2020-6: Mounted on FR4 Board using 30 mm<sup>2</sup>, 2 oz Cu.

### Recommended Operating Conditions (Note 6)

Symbol	Parameter	Min	Max	Unit
$V_{IN}$	Supply Voltage	3	30	V
$T_A$	Operating Ambient Temperature Range	-40	+85	$^\circ\text{C}$

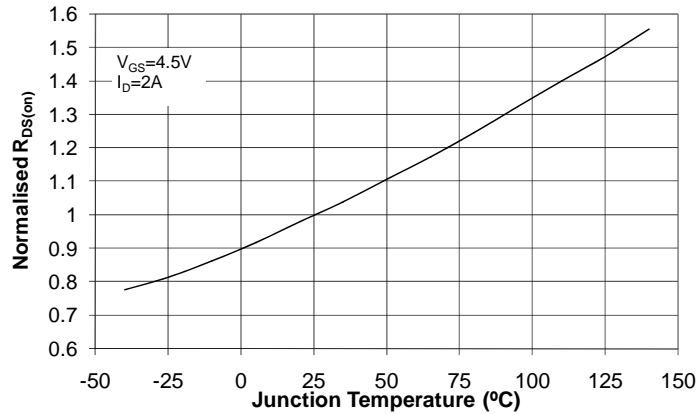
Note: 6. The device function is not guaranteed outside of the recommended operating conditions.

**Electrical Characteristics ( $V_{IN}$  (OVP\_SENSE) = 5.0V,  $T_J$  = +25°C, unless otherwise noted)**

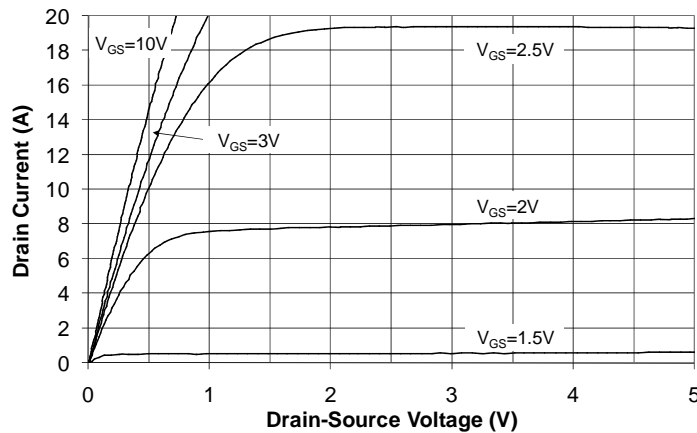
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
<b>Power FET</b>						
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$ $T_J = 85^\circ C$			1.0 10	$\mu A$
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 8V$			80	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.62	0.9	1.2	V
$R_{DS(on)}$	Drain-to-Source On-Resistance (Note 7)	$V_{GS} = 4.5V, I_D = 2.0A$ $V_{GS} = 2.5V, I_D = 2.0A$		41 55	53 68	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 5V, I_D = 2.0A$		8		S
$C_{ISS}$	Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1MHz$		500		pF
$C_{OSS}$	Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1MHz$		65		pF
$C_{RSS}$	Reverse Transfer Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1MHz$		50		pF
<b>LDO (unless otherwise noted, <math>T_J = 25^\circ C, V_{IN} = 5.0V</math>)</b>						
$V_{OUT}$	Regulated Output Voltage	$V_{IN} = 5.5V, I_{OUT} = 1mA$	4.6	5.0	5.3	V
$V_{head}$	Headroom	$V_{IN} - V_{OUT}, I_{OUT} = 1.2mA,$ $V_{IN} = 4.6V$			150	mV
		$V_{IN} - V_{OUT}, I_{OUT} = 10mA,$ $V_{IN} = 4.8V, T_J = -40$ to $+125^\circ C$			1000	mV
<b>Response to Input Transient</b>						
$t_{pulse}$	Time signal is above 5.5V	$V_{IN}$ 0 to 30V, < 1 $\mu s$ rise time, 5.0k $\Omega$ resistive load (Note 8)			5.0	$\mu s$
$V_{pk}$	Peak Voltage	$V_{IN}$ 0 to 30V, < 1 $\mu s$ rise time, 5.0k $\Omega$ resistive load (Note 8)			9.0	V
<b>Total Device</b>						
$I_{bias}$	Input Bias Current	$V_{IN} = 5.5V$		110	850	$\mu A$
$V_{IN\_min}$	Minimum Operating Voltage				3.0	V

Notes: 7. Pulse test width 300 $\mu s$ , duty cycle 2%  
8. Guaranteed by design

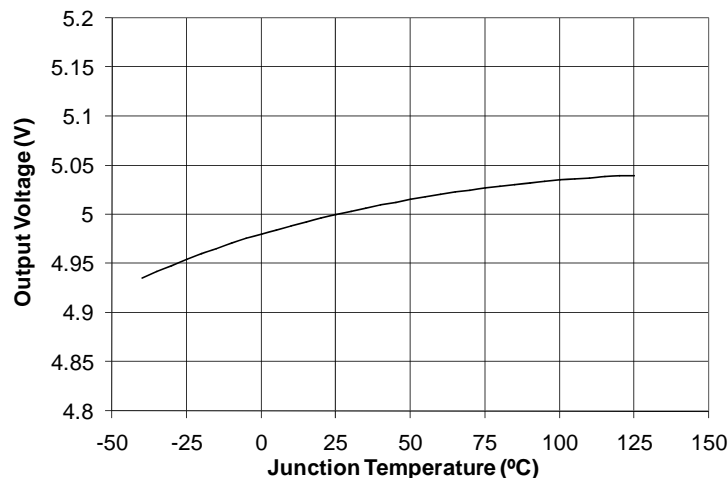
**Typical Performance Characteristics**



**Figure 3.  $R_{DS(on)}$  variation over junction temperature**



**Figure 4.  $R_{DS(on)}$  Characteristics**



**Figure 5. Output voltage variation over junction temperature**

## Applications Information

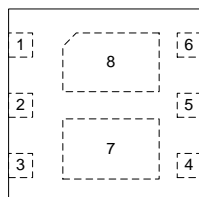
### Theory of Operation

The AP9050 was designed to work in close relationship with a PMIC (Power Management IC). To protect the PMIC from an overvoltage situation the AP9050 powers up a detection circuit within the connected PMIC. (See Figure 2 as reference)

This detection circuit determines if a valid input source is connected (ex.  $V_{IN} < 8V$ ). If a valid input source is detected the power MOSFET will be turned on and the supply current to the PMIC will be turned on. The overvoltage detection is continuous, if an overvoltage occurs at a later state the Power MOSFET will be turned off.

### PCB Layout

The AP9050 was designed utilizing two process technologies to provide best performance and a cost effective solution.



**Figure 6. Package Pin Out**

Both die are packaged side by side in the U-DFN2020-6 package and are mounted on two separate exposed pads. These pads are not required for electrical functionality, but to aid with the thermal performance of AP9050.

Attention should be paid in the layout of the PCB (Printed Circuit Board) that PAD7 is connected to  $V_{IN}$  of the LDO, pin 3, while PAD8 is connected to the Drain of the Power MOSFET, pin 6 of the package. For best thermal performance large copper areas connected to the two exposed pads should be used to transfer heat away from the AP9050.

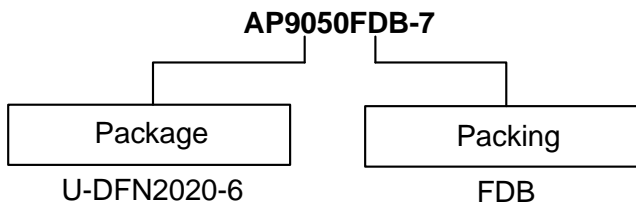
### External Capacitors

AP9050 was specified to reduce board space and external component count, by designing the LDO to be stable without an external bypass capacitor.

A low ESR 1nF to 10nF external capacitor can be used to improve behavior with fast ac transients or other switching currents that might be present.

To improve noise immunity and ac impedance from long input traces a 1nF capacitor can be added to the input  $V_{IN}$  of the LDO.

**Ordering Information**



Device	Package Code	Packaging (Note 10)	7" Tape and Reel	
			Quantity	Part Number Suffix
AP9050FDB-7	FDB	U-DFN2020-6	3000/Tape & Reel	-7

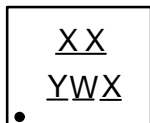


Note: 10. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

**Marking Information**

**U-DFN2020-6**

**( Top View )**

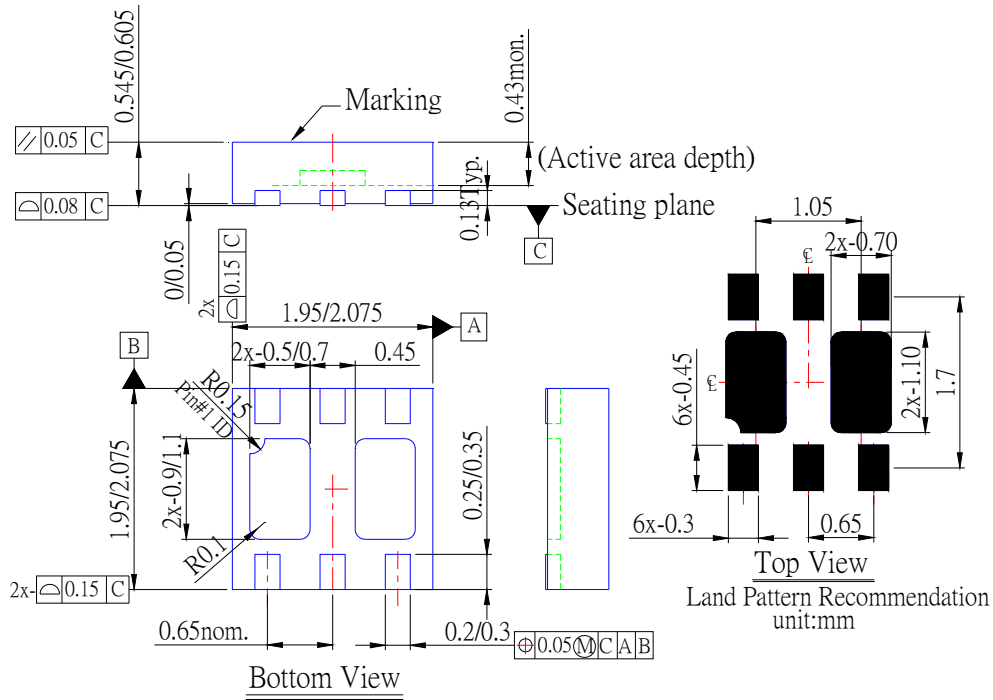


- XX : Identification Code
- Y : Year : 0~9
- W : Week : A~Z : 1~26 week;  
a~z : 27~52 week; z represents 52 and 53 week
- X : A~Z : Internal code

Device	Package	Identification Code
AP9050FDB	U-DFN2020-6	BZ

**Package Outline Dimensions (All Dimensions in mm)**

U-DFN2020-6



NEW PRODUCT



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